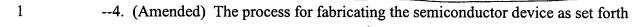
In the Claims:

Please amend claims 1, 4 and 8 in the following manner:

1	1. (Amended) A process for fabricating a semiconductor device having a
2/	buried layer comprising the steps of:
3	implanting an impurity ion [into] region below a surface of a substrate
4	where [the] a buried layer is to be formed in [a] the substrate;
5	[providing] placing the substrate inside a reactor furnace;
6	[preparing] providing a non-oxidizing atmosphere inside of the reactor
7	furnace;
8	annealing the substrate to activate and diffuse the implanted impurity ion
9	region while increasing [inside] the internal temperature of the reactor furnace up to a
10	first temperature; and
11	before the ion implanted region beneath the surface of the substrate
12	expands sufficiently to reach the surface of the substrate, changing [shifting] the [inside]
13	internal temperature of the reactor furnace from the first temperature to a second
14	temperature [in] at which [a] an epitaxial crystal starts to grow on the surface and
15	introducing [a] an epitaxial growth gas into the reactor furnace to [grow] cause an
16	epitaxial layer to grow on [a] the surface of the substrate



² in claim 1 further comprising the steps of:

